

N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK Rev. 2 — 2 March 2012 Product data s

Product data sheet

#### **Product profile** 1.

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#### **1.1 General description**

Standard level N-channel MOSFET in a D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	-	-	89	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	211	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	8.16	9.6	mΩ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 60 A; V <sub>DS</sub> = 50 V;	-	23	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14;see Figure 15	-	82	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 89 A; $V_{sup}$ ≤ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	-	177	mJ

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#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	_	_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package			
	Name	Description	Version	
PSMN9R5-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404	

### 4. Limiting values

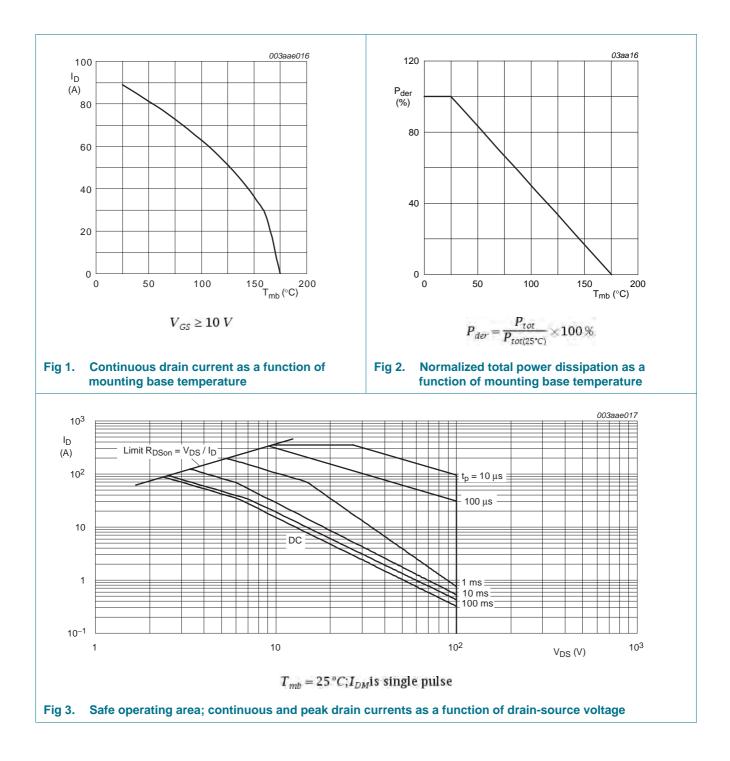
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
drain-gate voltage	T <sub>j</sub> ≤ 175 °C; T <sub>j</sub> ≥ 25 °C; R <sub>GS</sub> = 20 kΩ	-	100	V
gate-source voltage		-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	63	А
	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	89	А
peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>	-	355	А
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	211	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
peak soldering temperature		-	260	°C
diode				
source current	T <sub>mb</sub> = 25 °C	-	89	А
peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	355	А
lgedness				
non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 89 A; $V_{sup} \le$ 100 V; unclamped; $R_{GS}$ = 50 $\Omega$	-	177	mJ
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature peak soldering temperature cliode source current peak source current peak source current peak source current peak source current	$\begin{array}{ll} \mbox{drain-source voltage} & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C} \\ \mbox{drain-gate voltage} & T_j \le 175 \ {}^\circ\mbox{C}; \ R_{GS} = 20 \ k\Omega \\ \mbox{gate-source voltage} \\ \mbox{drain current} & V_{GS} = 10 \ V; \ T_{mb} = 100 \ {}^\circ\mbox{C}; \ see \ Figure 1} \\ \mbox{V}_{GS} = 10 \ V; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 1} \\ \mbox{pulsed; } t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2} \\ \mbox{storage temperature} \\ \mbox{junction temperature} \\ \mbox{peak source current} & T_{mb} = 25 \ {}^\circ\mbox{C}; \ see \ Figure 2} \\ \mbox{source current} & T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{pulsed; } t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{gates source current} & T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{pulsed; } t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ {}^\circ\mbox{C} \\ \mbox{pulsed; } t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{pulsed; } t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{peak source current} & Pulsed; \ t_p \le 10 \ \mu\mbox{s}; \ T_{mb} = 25 \ {}^\circ\mbox{C} \\ \mbox{pulsed; } t_p \le 10 \ V; \ T_{j(init)} = 25 \ {}^\circ\mbox{C}; \ l_D = 89 \ A; \\ \end{tabular}$	$\begin{array}{cccc} drain-source \mbox{ voltage } & T_j \ge 25 \ {}^\circ\mbox{C}; \ T_j \le 175 \ {}^\circ\mbox{C} & - & & & & & & & & & & & & & & & & & $	$\begin{array}{cccc} drain-source \ voltage & T_j \ge 25\ ^{\circ}C;\ T_j \le 175\ ^{\circ}C & - & 100 \\ drain-gate \ voltage & T_j \le 175\ ^{\circ}C;\ T_j \ge 25\ ^{\circ}C;\ R_{GS} = 20\ k\Omega & - & 100 \\ gate-source \ voltage & -20 & 20 \\ drain \ current & V_{GS} = 10\ V;\ T_{mb} = 100\ ^{\circ}C;\ see\ Figure\ 1 & - & 63 \\ \hline V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 1 & - & 89 \\ peak\ drain\ current & pulsed;\ t_p \le 10\ \mu s;\ T_{mb} = 25\ ^{\circ}C; \\ see\ Figure\ 3 & - & 211 \\ storage\ temperature & T_{mb} = 25\ ^{\circ}C;\ see\ Figure\ 2 & - & 211 \\ storage\ temperature & -55 & 175 \\ junction\ temperature & -55 & 175 \\ peak\ soldering\ temperature & -55 & 175 \\ peak\ soldering\ temperature & - & 260 \\ \hline diode & & & & \\ source\ current & T_{mb} = 25\ ^{\circ}C & - & 89 \\ peak\ source\ current & T_{mb} = 25\ ^{\circ}C & - & 89 \\ peak\ source\ current & T_{mb} = 25\ ^{\circ}C & - & 89 \\ peak\ source\ current & V_{GS} = 10\ V;\ T_{mb} = 25\ ^{\circ}C;\ I_D = 89\ A; & - & 177 \end{array}$

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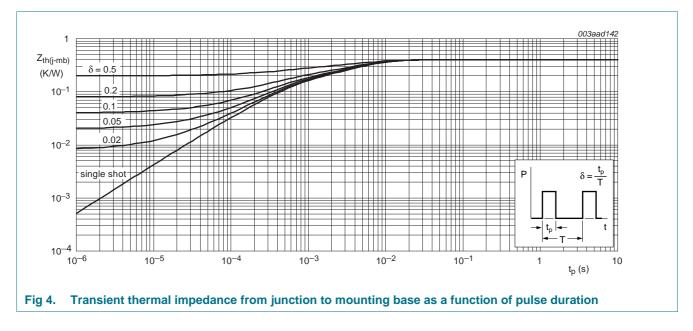
# PSMN9R5-100BS



#### N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK

#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



#### Table 5 Thermal characteristics

PSMN9R5-100BS

#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.8	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	100	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	4	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	17.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	23.5	27.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	8.16	9.6	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 A$ ; $V_{DS} = 0 V$ ; $V_{GS} = 10 V$ ; see Figure 14	-	67	-	nC
		$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	82	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	21	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 3 \text{ V};$ see Figure 14	-	13.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge	$I_D = 60 \text{ A}; \text{ V}_{DS} = 50 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$ see Figure 14	-	7.8	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	23	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.5	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4454	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	302	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	185	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 0.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	22	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ T_{j} = 25 \ ^{\circ}C$	-	25.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	52.2	-	ns
t <sub>f</sub>	fall time		-	22.8	-	ns

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Source-drain diode

# PSMN9R5-100BS

Тур

Max

Unit

#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

Min

V <sub>SD</sub>	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 17</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; \text{ d}I_S/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	61.5	-	ns
Qr	recovered charge	$V_{DS} = 50 V$	-	157	-	nC
30 R <sub>DSon</sub> (mΩ) 24		003aae025 C (pF) 6000			003aae022 C <sub>iss</sub>	
18		2000			C <sub>rss</sub>	
6 4	8 12 $T_j = 25 \ ^{\circ}C; I_D = 20$	V <sub>GS</sub> (V)	$3 \qquad 6$ $V_{DS} = 0 V; f = 1$		12 (V)	
	n-source on-state resist te-source voltage; typic		reverse transf of gate-source			
150 g <sub>fs</sub> (S) 100 50		003aae021 100 lp (A) 75 50 25	10 5.5		003aaae019 5 4.8 4.7 4.5	
0 0	$T_j = 25 ^\circ C; V_{DS} = 25$	I <sub>D</sub> (A)	$T_{j} = 25 ^{\circ}C$	1.5	4.3	
	ard transconductance a current; typical values		aracteristics: of drain-source			

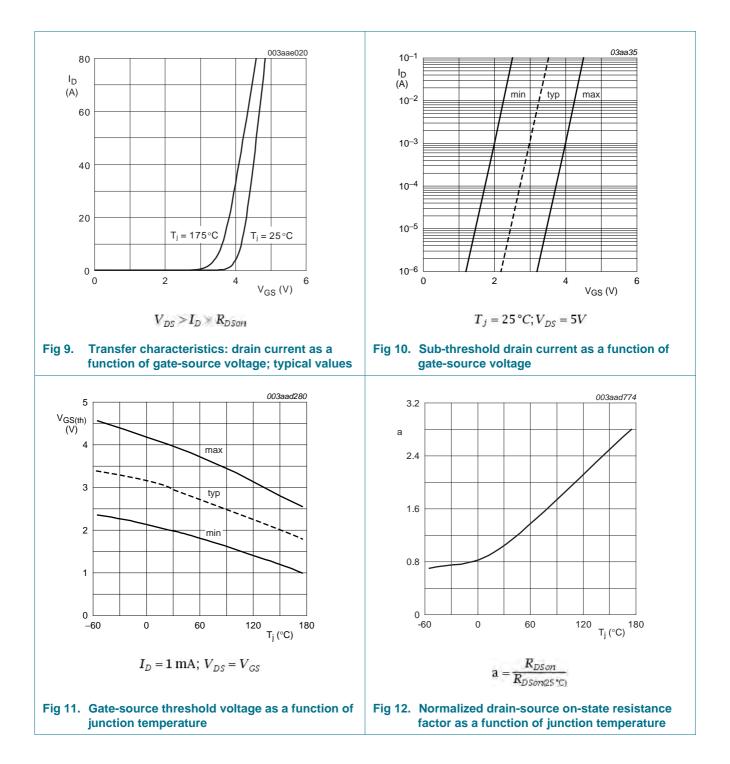
#### Table 6. Characteristics ...continued

Parameter

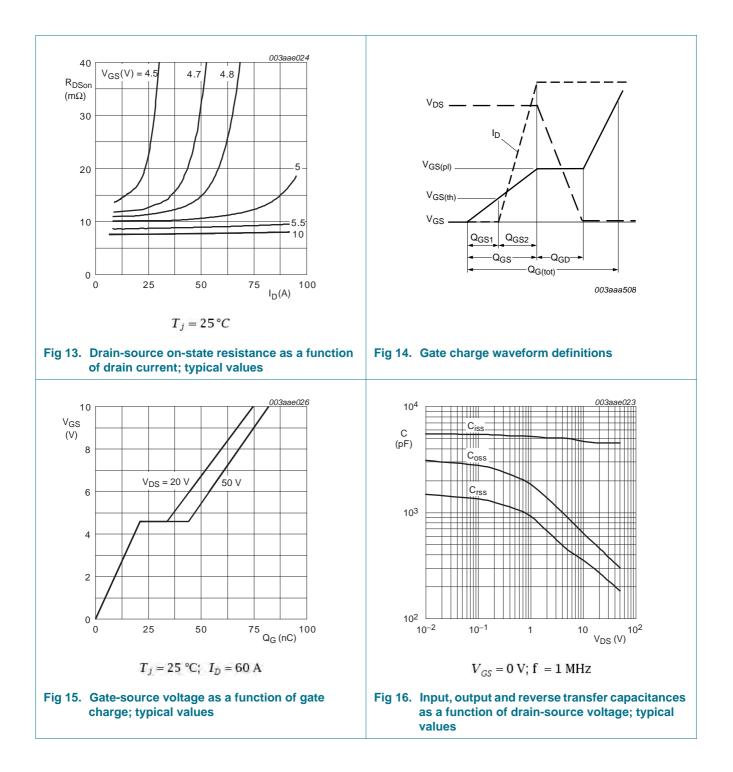
Conditions

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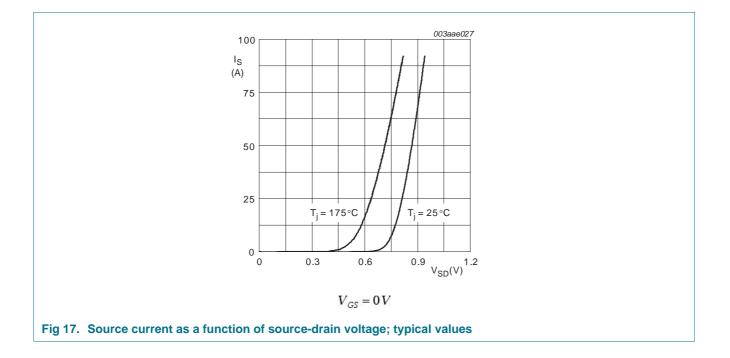
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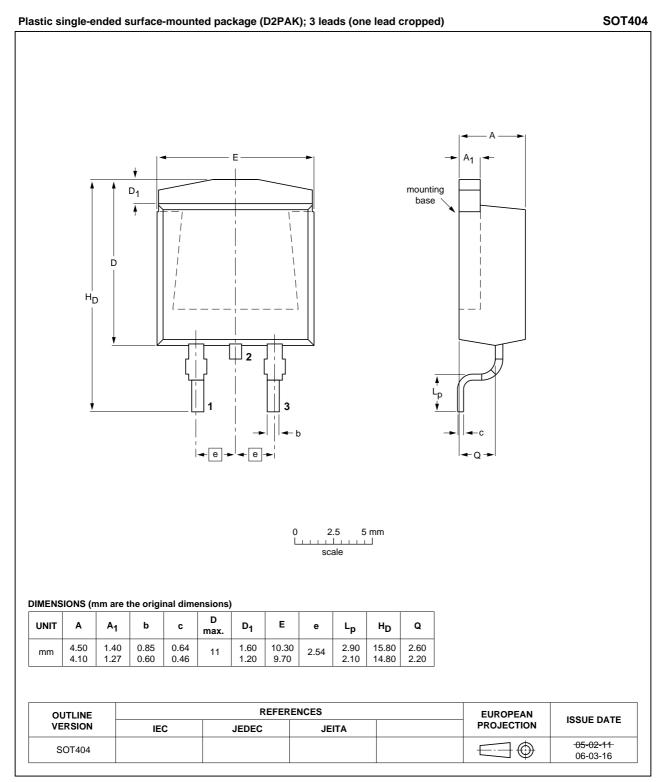


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#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

### 7. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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PSMN9R5-100BS

#### N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK

### 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R5-100BS v.2	20120302	Product data sheet	-	PSMN9R5-100BS v.1
Modifications:	<ul> <li>Status changed</li> </ul>	from objective to product.		
	<ul> <li>Various changes</li> </ul>	s to content.		
PSMN9R5-100BS v.1	20111025	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

PSMN9R5-100BS

#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

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#### N-channel 100 V 9.6 m $\Omega$ standard level MOSFET in D2PAK

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